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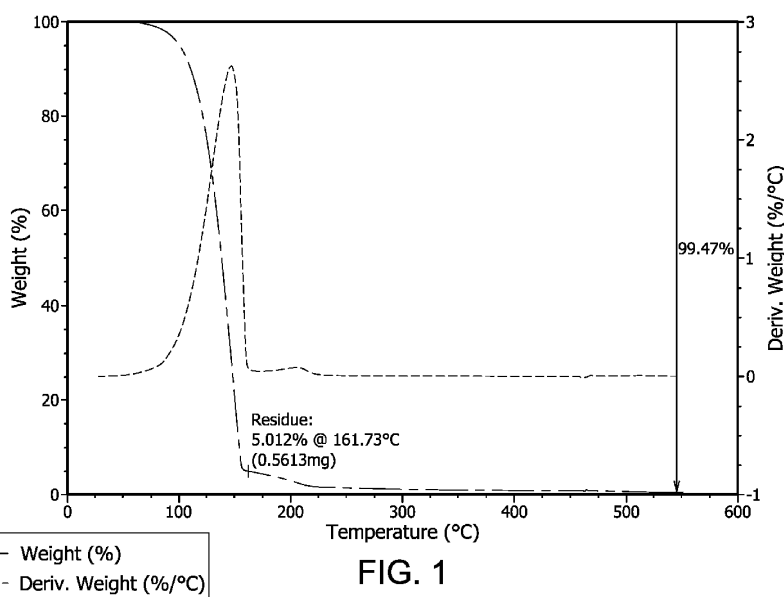
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(54) Title: SILANOLS AND SILANEDIOLS



(57) Abstract: A composition useful in depositing low dielectric constant (low k) insulating materials into high aspect ratio gaps, trenches, vias, and other surface features, of semiconductor devices by Atomic Layer Deposition (ALD) or Chemical Vapor Deposition (CVD) processes is disclosed. A first composition may comprise an alkoxysilanediol. The alkoxy-based substituent of the silanediol may be a branched, or cyclic, alkyl group having between 3 to 10 carbon atoms. In another instance, the composition may comprise an alkoxysilanol. The alkoxy-based substituent of the silanol may be a branched, or cyclic, alkyl group having between 3 to 10 carbon atoms.

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